Wenhao Chen

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/7554669/publications.pdf

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21	538	758635 12	887659 17
papers	citations	h-index	g-index

22	22	22	974
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Volatile and Non-Volatile Switching in Cu-SiO₂Programmable Metallization Cells. IEEE Electron Device Letters, 2016, 37, 580-583.	2.2	87
2	Low-Temperature Characteristics of HfO_{<italic>x</italic>}-Based Resistive Random Access Memory. IEEE Electron Device Letters, 2015, 36, 567-569.	2.2	85
3	A CMOS-compatible electronic synapse device based on Cu/SiO₂/W programmable metallization cells. Nanotechnology, 2016, 27, 255202.	1.3	66
4	Total ionizing dose effect of Î³-ray radiation on the switching characteristics and filament stability of HfOx resistive random access memory. Applied Physics Letters, 2014, 104, .	1.5	57
5	In Situ TEM Imaging of Defect Dynamics under Electrical Bias in Resistive Switching Rutile-TiO₂. Microscopy and Microanalysis, 2015, 21, 140-153.	0.2	42
6	SiO2 based conductive bridging random access memory. Journal of Electroceramics, 2017, 39, 109-131.	0.8	32
7	Dislocation impact on resistive switching in single-crystal SrTiO3. Journal of Applied Physics, 2013, 113, .	1.1	24
8	A Study of Gamma-Ray Exposure of Cuâ€“SiO$_2$ Programmable Metallization Cells. IEEE Transactions on Nuclear Science, 2015, 62, 2404-2411.	1.2	24
9	Elimination of high transient currents and electrode damage during electroformation of TiO₂-based resistive switching devices. Journal Physics D: Applied Physics, 2012, 45, 395101.	1.3	20
10	Fabrication and luminescent properties of red phosphor M3BO6:Eu3+(M=La, Y). Journal of Rare Earths, 2010, 28, 295-298.	2.5	18
11	Radiation Hardening by Process of CBRAM Resistance Switching Cells. IEEE Transactions on Nuclear Science, 2016, 63, 2145-2151.	1.2	15
12	Low-Temperature Characterization of Cuâ€“Cu:Silica-Based Programmable Metallization Cell. IEEE Electron Device Letters, 2017, 38, 1244-1247.	2.2	15
13	Demonstration of spike timing dependent plasticity in CBRAM devices with silicon neurons. , 2016, , .		12
14	Total-Ionizing-Dose Effects on Resistance Stability of Programmable Metallization Cell Based Memory and Selectors. IEEE Transactions on Nuclear Science, 2017, 64, 269-276.	1.2	11
15	Impedance Spectroscopy of Programmable Metallization Cells With a Thin SiO₂Switching Layer. IEEE Electron Device Letters, 2016, 37, 576-579.	2.2	9
16	Flexible Ag-ChG Radiation Sensors: Limit of Detection and Dynamic Range Optimization Through Physical Design Tuning. IEEE Transactions on Nuclear Science, 2016, 63, 2137-2144.	1.2	7
17	TID Impact on Process Modified CBRAM Cells. , 2015, , .		6
18	<italic>In Situ</italic> Synaptic Programming of CBRAM in an Ionizing Radiation Environment. IEEE Transactions on Nuclear Science, 2018, 65, 192-199.	1.2	5

#	Article	IF	Citations
19	Ag-chalcogenide glass flexible radiation sensor: Impact of atomic ratio of Se on the TID influenced lateral diffusion of Ag. , 2016, , .		1
20	A Comparative Study on TID Influenced Lateral Diffusion of Group 11 Metals into GexS_{1-x}and Ge_xSe_{1-x} Systems: A Flexible Radiation Sensor Development Perspective. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	0
21	SiO2-Based Conductive-Bridging Random Access Memory. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 147-186.	0.3	0